

CLAIMS:

1. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon in contact with a silicon nitride film;

forming a continuous layer of a material including a catalyst capable of promoting a crystallization of silicon onto at least a portion of said semiconductor film;

heating said semiconductor film in order to crystallize said semiconductor film; and then

irradiating said semiconductor film with light in order to improve the crystallinity of said semiconductor film.

10

Sub  
B<sub>1</sub>  
5

Add  
B<sub>2</sub>

Add D<sub>1</sub>

Add E<sub>4</sub>

Add F<sub>7</sub>

Add G<sub>1</sub>

Add H<sub>1</sub>

Add L<sub>1</sub>